TECHNICAL DATA DATA SHEET 892, REV. -

HERMETIC POWER MOSFET N-CHANNEL

- 200 VOLT, 0.4 OHM, 9.0A MOSFET
- Fast Switching
- Low R_{DS (on)}
- Equivalent to IRFY230M

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_A = 25$ °C UNLESS OTHERWISE SPECIFIED.

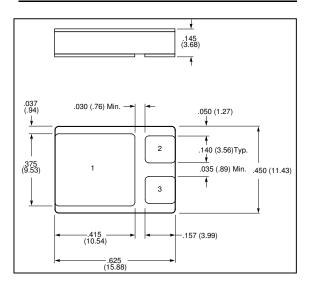
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT @ T _C = 25°C	I _D	-	-	9.0	Amps
PULSED DRAIN CURRENT @ T _C = 25°C	I _{DM}	-	-	36	Amps(pk)
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	1.27	°C/W
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P_{D}	-	-	98	Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV_{DSS}	200	-	-	Volts
$V_{GS} = 0V, I_{D} = 1.0mA$					
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250\mu A$	$V_{GS(th)}$	2.0	-	4.0	Volts
DRAIN TO SOURCE ON STATE RESISTANCE					
$V_{GS} = 10 Vdc, I_{D} = 6.0 A$	$R_{DS(ON)}$	-	-	0.4	Ω
$I_D = 9.0A$				0.49	
ZERO GATE VOLTAGE DRAIN CURRENT		-	-		
$V_{DS} = 0.8xMax$. Rating, $V_{GS} = 0Vdc$	I_{DSS}			25	μΑ
$V_{DS} = 0.8xMax$. Rating					
$V_{GS} = 0Vdc, T_J = 125^{\circ}C$				250	
GATE TO BODY LEAKAGE CURRENT $V_{GS} = \pm 20 V dc$,	I_{GSS}	-	-	±100	nA
TOTAL GATE CHARGE $V_{GS} = 10 \text{ Vdc}$	Q_g	16	-	39	nC
GATE TO SOURCE CHARGE $V_{DS} = 0.5V$ Max. Rating,	Q_gs	3.0		5.7	
GATE TO DRAIN CHARGE $I_D = 9.0A$	Q_gd	5.5		20	
TURN ON DELAY TIME $V_{DD} = 100V$,	$t_{d(ON)}$	-	-	35	nsec
RISE TIME $I_D = 9.0A$,	t _r			80	
TURN OFF DELAY TIME $R_G = 7.5\Omega$	$t_{d(OFF)}$			60	
FALL TIME $V_{GS} = 10V$	t _f			40	
FORWARD VOLTAGE $T_J = 125$ °C, $I_S = 9.0$ A, $V_{GS} = 0$ V	$V_{\sf SD}$	-	-	1.4	Volts
REVERSE RECOVERY TIME $I_S = 9.0A$,	t_{rr}	-	-	500	nsec
REVERSE RECOVERY CHARGE di/dt ≤ 100A/μsec,					
$V_{DD} \leq 50V$					
INPUT CAPACITANCE $V_{DS} = 25 \text{ Vdc},$	C_{iss}	-	600	-	pF
OUTPUT CAPACITANCE $V_{GS} = 0 \text{ Vdc},$	C_{oss}		250		
REVERSE TRANSFER CAPACITANCE f = 1 MHz	C_{rss}		80		

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MECHANICAL DIMENSIONS: in Inches / mm



LCC-3P

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
N CHANNEL MOSFET IN A	DRAIN	SOURCE	GATE
LCC-3P PACKAGE			



TECHNICAL DATA

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